

## 1. General description

Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switched-mode power supplies.



## 2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

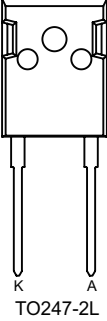
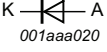
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{RRM}$	repetitive peak reverse voltage			650			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 103$ °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		20			A
$T_j$	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_F$	forward voltage	$I_F = 20$ A; $T_j = 25$ °C; <a href="#">Fig. 5</a>		-	1.45	1.70	V
		$I_F = 20$ A; $T_j = 150$ °C; <a href="#">Fig. 5</a>		-	1.80	2.20	V
<b>Dynamic characteristics</b>							
$Q_r$	recovered charge	$I_F = 20$ A; $di_F/dt = 500$ A/ $\mu$ s; $V_R = 400$ V; $T_j = 25$ °C; <a href="#">Fig. 7</a>		-	28	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
mb	mb	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC5D20650W	TO247-2L	WNSC5D20650W6Q	Tube	30	TO247L-2L	10-Nov-2020

## 7. Marking

Table 4. Marking codes

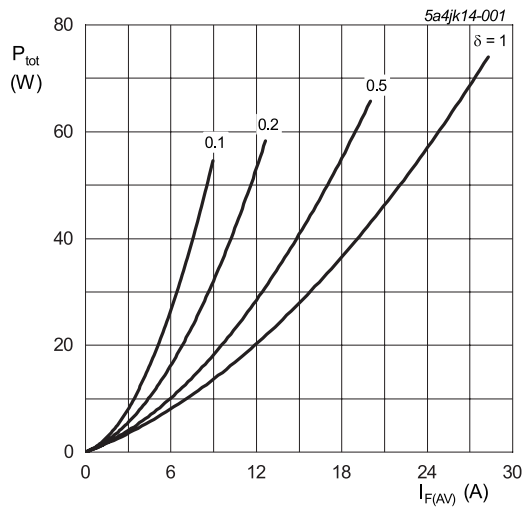
Type number	Marking codes
WNSC5D20650W	WNSC5D 20650W

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

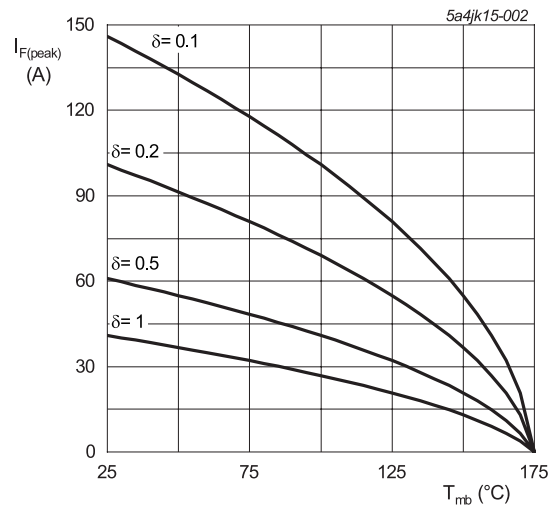
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{RWM}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 103\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>		20	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_{mb} \leq 103\text{ }^\circ\text{C}$ ; square-wave pulse		40	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse		100	A
		$t_p = 10\text{ }\mu\text{s}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; square-wave pulse		825	A
$I^2t$	$I^2t$ for fusing	sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$		50	$\text{A}^2\text{s}$
$T_{stg}$	storage temperature			-55 to 175	$^\circ\text{C}$
$T_j$	junction temperature			-55 to 175	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.004\text{ V}; R_s = 0.0570\text{ }\Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values**



**Fig. 2. Current derating as a function of mounting base temperature**

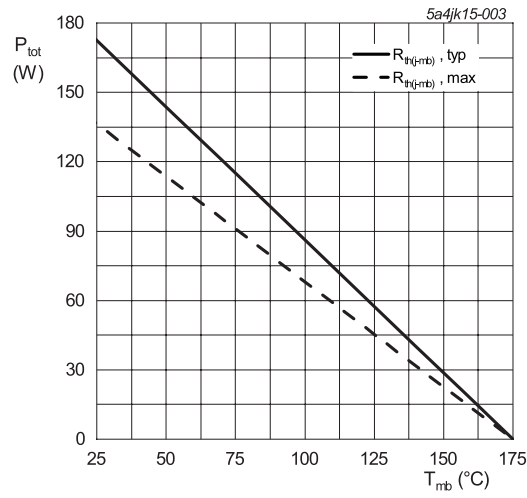


Fig. 3. Total power dissipation as a function of mounting base temperature

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>		-	0.87	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

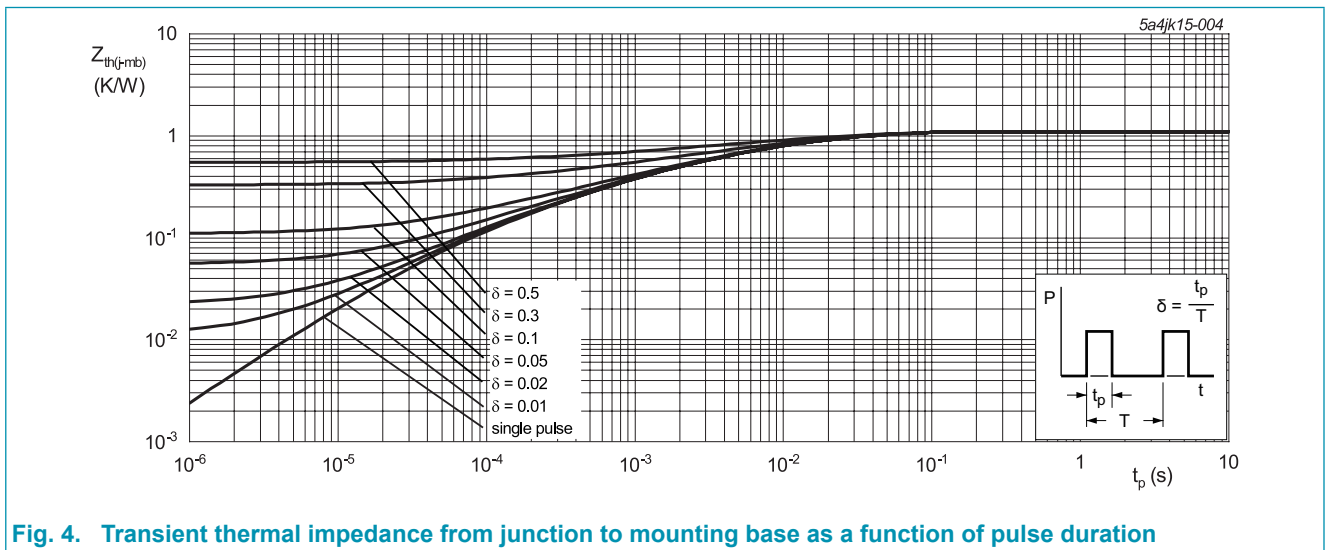
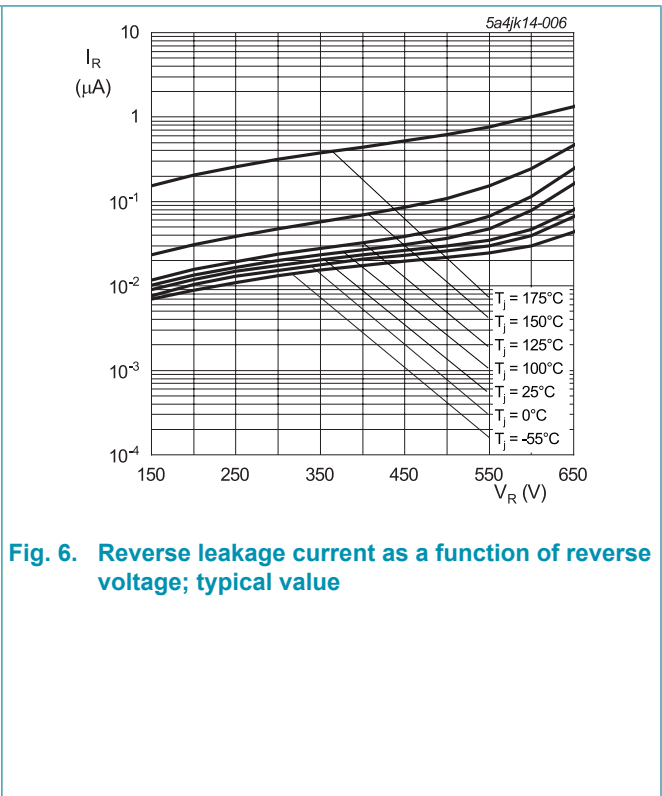
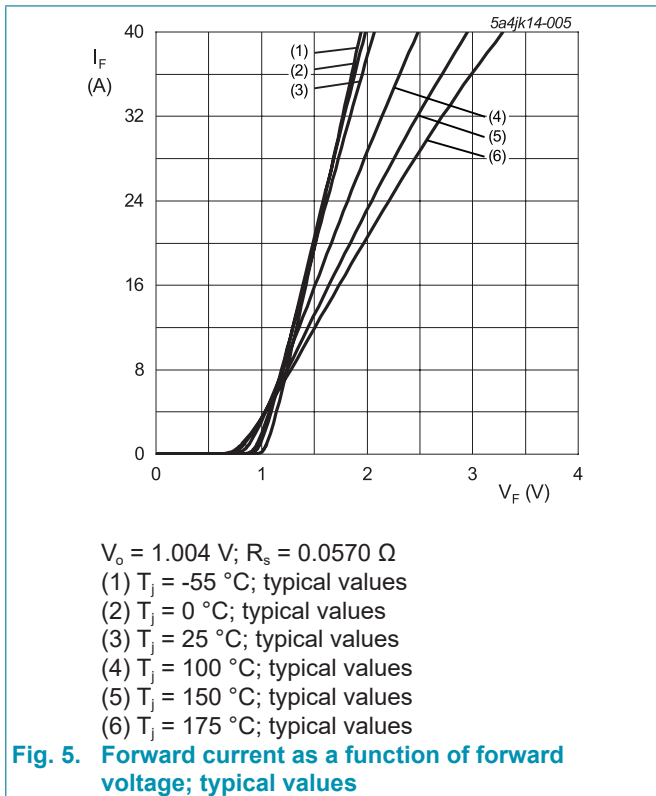


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_F$	forward current	$I_F = 20\text{ A}; T_J = 25\text{ }^\circ\text{C}; \text{Fig. 5}$		-	1.45	1.70	V
		$I_F = 20\text{ A}; T_J = 150\text{ }^\circ\text{C}; \text{Fig. 5}$		-	1.80	2.20	V
		$I_F = 20\text{ A}; T_J = 175\text{ }^\circ\text{C}; \text{Fig. 5}$		-	2.00	2.30	V
$I_R$	reverse current	$V_R = 650\text{ V}; T_J = 25\text{ }^\circ\text{C}; \text{Fig. 6}$		-	1	100	$\mu\text{A}$
		$V_R = 650\text{ V}; T_J = 175\text{ }^\circ\text{C}; \text{Fig. 6}$		-	30	500	$\mu\text{A}$
<b>Dynamic characteristics</b>							
$Q_r$	recovered charge	$I_F = 20\text{ A}; V_R = 400\text{ V}; di_F/dt = 500\text{ A}/\mu\text{s}; T_J = 25\text{ }^\circ\text{C}; \text{Fig. 7}$		-	28	-	nC
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 1\text{ V}; T_J = 25\text{ }^\circ\text{C}$		-	620	-	pF
		$f = 1\text{ MHz}; V_R = 300\text{ V}; T_J = 25\text{ }^\circ\text{C}$		-	70	-	pF
		$f = 1\text{ MHz}; V_R = 600\text{ V}; T_J = 25\text{ }^\circ\text{C}$		-	68	-	pF
$E_{as}$	non-repetitive avalanche energy	$I_R = 6.3\text{ A}; L = 5\text{ mH}; T_{j(\text{init})} = 25\text{ }^\circ\text{C}$		100	-	-	mJ



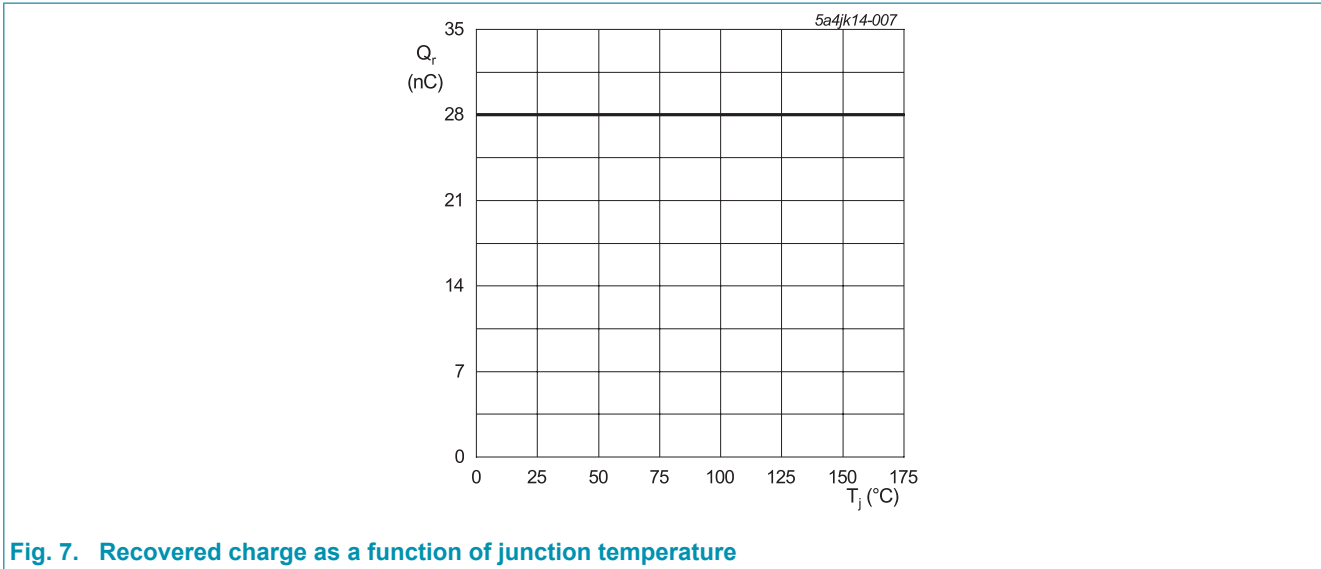
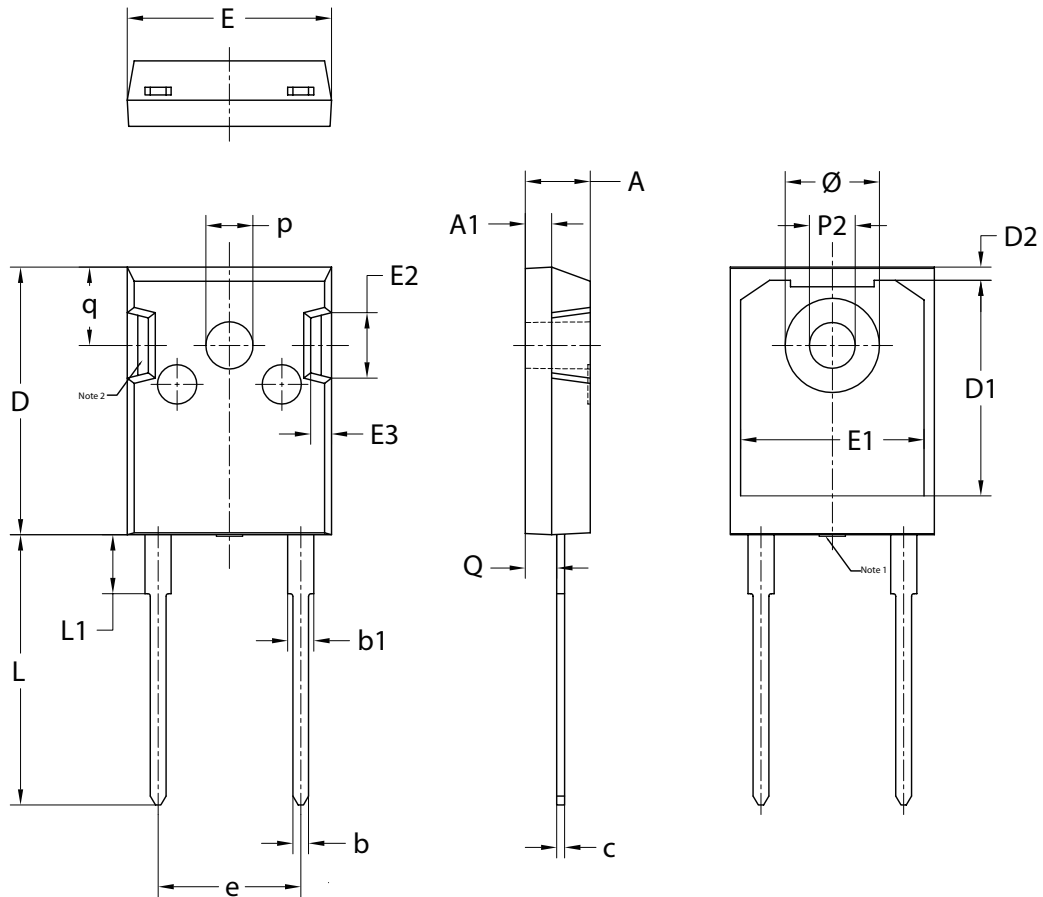


Fig. 7. Recovered charge as a function of junction temperature

### 11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 2 leads TO-247

TO247-2L



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	c	D	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	E <sub>2</sub>	E <sub>3</sub>	e	L	L <sub>1</sub>	P <sub>2</sub>	p	Q	q	Ø
mm	<u>5.20</u>	<u>2.10</u>	<u>1.40</u>	<u>2.20</u>	<u>0.70</u>	<u>20.60</u>	<u>16.20</u>	<u>1.20</u>	<u>15.75</u>	<u>14.22</u>	<u>5.20</u>	<u>1.80</u>	<u>10.90</u>	<u>20.72</u>	<u>4.75</u>	<u>3.60</u>	<u>3.70</u>	<u>2.60</u>	<u>6.18</u>	<u>7.30</u>
	4.70	1.90	1.00	1.80	0.50	20.30	16.87	0.80	15.45	13.82	4.80	1.40	BSC	20.22	4.25	3.40	3.50	2.20	5.78	7.10

- Note:
1. Mold resin protrusion max 0.127mm.
  2. Metal exposed with Sn plating.



## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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